

128MB - 16Mx64, SDRAM UNBUFFERED

FEATURES

- PC100 and PC133 compatible
- Burst Mode Operation
- Auto and Self Refresh capability
- LVTTTL compatible inputs and outputs
- Serial Presence Detect with EEPROM
- Fully synchronous: All signals are registered on the positive edge of the system clock
- Programmable Burst Lengths: 1, 2, 4, 8 or Full Page
- 3.3V ± 0.3V Power Supply
- 168 Pin DIMM JEDEC
 - D2: 30.48mm (1.20")

DESCRIPTION

The W3DG6418V is a 16Mx64 synchronous DRAM module which consists of eight 16Mx8 SDRAM components in TSOP II package and one 2K EEPROM in an 8 Pin TSSOP package for Serial Presence Detect which are mounted on a 168 Pin DIMM multilayer FR4 Substrate.

* This product is under development, is not qualified or characterized and is subject to change without notice.

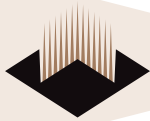
NOTE: Consult factory for availability of:

- RoHS compliant products
- Vendor source control options
- Industrial temperature option

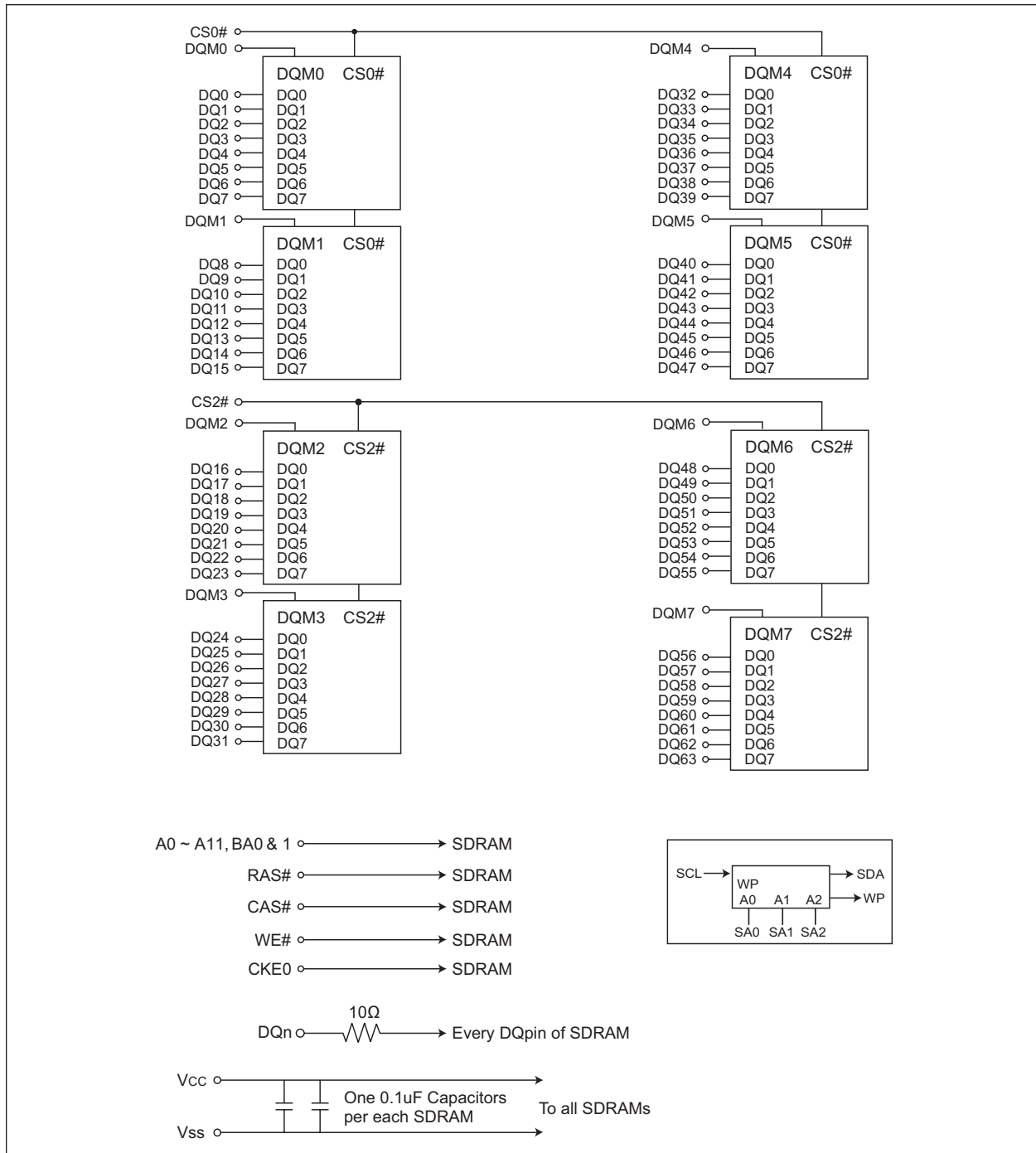
PIN CONFIGURATIONS (FRONT SIDE/BACK SIDE)												PIN NAMES	
Pin	Front	Pin	Front	Pin	Front	Pin	Back	Pin	Back	Pin	Back		
1	Vss	29	DQM1	57	DQ18	85	Vss	113	DQM5	141	DQ50	A0 - A11	Address input (Multiplexed)
2	DQ0	30	CS0#	58	DQ19	86	DQ32	114	CS1#	142	DQ51	BA0-1	Select Bank
3	DQ1	31	DNU	59	Vcc	87	DQ33	115	RAS#	143	Vcc	DQ0-63	Data Input/Output
4	DQ2	32	Vss	60	DQ20	88	DQ34	116	Vss	144	DQ52	CLK0, CLK1, CLK2, CLK3	Clock input
5	DQ3	33	A0	61	NC	89	DQ35	117	A1	145	NC	CKE0	Clock Enable input
6	Vcc	34	A2	62	VREF*	90	Vcc	118	A3	146	VREF*	CS0# - CS2#	Chip select Input
7	DQ4	35	A4	63	CKE1*	91	DQ36	119	A5	147	DNU	RAS#	Row Address Strobe
8	DQ5	36	A6	64	Vss	92	DQ37	120	A7	148	Vss	CAS#	Column Address Strobe
9	DQ6	37	A8	65	DQ21	93	DQ38	121	A9	149	DQ53	WE#	Write Enable
10	DQ7	38	A10/AP	66	DQ22	94	DQ39	122	BA0	150	DQ54	DQM0-7	DQM
11	DQ8	39	BA1	67	DQ23	95	DQ40	123	A11	151	DQ55	Vcc	Power Supply (3.3V)
12	Vss	40	Vcc	68	Vss	96	Vss	124	Vcc	152	Vss	Vss	Ground
13	DQ9	41	Vcc	69	DQ24	97	DQ41	125	CLK1	153	DQ56	SDA	Serial data I/O
14	DQ10	42	CLK0	70	DQ25	98	DQ42	126	A12*	154	DQ57	SCL	Serial clock
15	DQ11	43	Vss	71	DQ26	99	DQ43	127	Vss	155	DQ58	DNU	Do not use
16	DQ12	44	DNU	72	DQ27	100	DQ44	128	CKE0	156	DQ59	NC	No Connect
17	DQ13	45	CS2#	73	Vcc	101	DQ45	129	CS3#*	157	Vcc	WP	Write Protect
18	Vcc	46	DQM2	74	DQ28	102	Vcc	130	DQM6	158	DQ60		
19	DQ14	47	DQM3	75	DQ29	103	DQ46	131	DQM7	159	DQ61		
20	DQ15	48	DNU	76	DQ30	104	DQ47	132	A13*	160	DQ62		
21	CB0*	49	Vcc	77	DQ31	105	CB4*	133	Vcc	161	DQ63		
22	CB1*	50	NC	78	Vss	106	CB5*	134	NC	162	Vss		
23	Vss	51	NC	79	CLK2	107	Vss	135	NC	163	CLK3		
24	NC	52	CB2*	80	NC	108	NC	136	CB6*	164	NC		
25	NC	53	CB3*	81	WP***	109	NC	137	CB7*	165	SA0**		
26	Vcc	54	Vss	82	SDA**	110	Vcc	138	Vss	166	SA1**		
27	WE#	55	DQ16	83	SCL**	111	CAS#	139	DQ48	167	SA2**		
28	DQM0	56	DQ17	84	Vcc	112	DQM4	140	DQ49	168	Vcc		

** These pins should be NC in the system which does not support SPD.

*** WP available on the WED3DG6318V-D2.



FUNCTIONAL BLOCK DIAGRAM





ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Voltage on any pin relative to V _{SS}	V _{IN} , V _{OUT}	-1.0 ~ 4.6	V
Voltage on V _{CC} supply relative to V _{SS}	V _{CC} , V _{CCQ}	-1.0 ~ 4.6	V
Storage Temperature	TSTG	-55 ~ +150	°C
Power Dissipation	PD	8	W
Short Circuit Current	IOS	50	mA

Note: Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded.
 Functional operation should be restricted to recommended operating condition.
 Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

Voltage Referenced to: V_{SS} = 0V, 0°C ≤ T_A ≤ +70°C

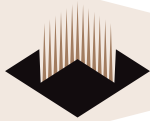
Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply Voltage	V _{CC}	3.0	3.3	3.6	V	
Input High Voltage	V _{IH}	2.0	3.0	V _{CCQ} +0.3	V	1
Input Low Voltage	V _{IL}	-0.3	—	0.8	V	2
Output High Voltage	V _{OH}	2.4	—	—	V	I _{OH} = -2mA
Output Low Voltage	V _{OL}	—	—	0.4	V	I _{OL} = -2mA
Input Leakage Current	I _{LI}	-10	—	10	µA	3

Note:
 1. V_{IH} (max)= 5.6V AC. The overshoot voltage duration is ≤ 3ns.
 2. V_{IL} (min)= -2.0V AC. The undershoot voltage duration is ≤ 3ns.
 3. Any input 0V ≤ V_{IN} ≤ V_{CC}
 Input leakage currents include Hi-Z output leakage for all bi-directional buffers with Tri-State outputs.

CAPACITANCE

T_A = 25°C, f = 1MHz, V_{CC} = 3.3V, V_{REF}=1.4V ± 200mV

Parameter	Symbol	Max	Unit
Input Capacitance (A0-A11)	C _{IN1}	35.5	pF
Input Capacitance (RAS#,CAS#,WE#)	C _{IN2}	35.5	pF
Input Capacitance (CKE0)	C _{IN3}	35.5	pF
Input Capacitance (CLK0-CLK3)	C _{IN4}	10	pF
Input Capacitance (CS0#, CS2#)	C _{IN5}	20	pF
Input Capacitance (DQM0-DQM7)	C _{IN6}	7	pF
Input Capacitance (BA0-BA1)	C _{IN7}	35.5	pF
Data input/output capacitance (DQ0-DQ63)	C _{OUT}	15	pF



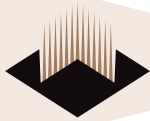
OPERATING CURRENT CHARACTERISTICS

$V_{CC} = 3.3V, 0^{\circ}C \leq T_A \leq 70^{\circ}C$

Parameters	Symbol	Conditions	Versions		Units	Note
			133	100		
Operating Current (One bank active)	I _{CC1}	Burst Length = 1 t _{RC} ≥ t _{RC(min)} I _{OL} = 0mA	720	720	mA	1
Precharge Standby Current in Power Down Mode	I _{CC2P}	CKE ≤ V _{IL(max)} , t _{CC} = 10ns	16		mA	
	I _{CC2PS}	CKE & CK ≤ V _{IL(max)} , t _{CC} = ∞	16		mA	
Precharge Standby Current in Non-Power Down Mode	I _{CC2N}	CKE ≥ V _{IH(min)} , CS ≥ V _{IH(min)} , t _{CC} = 10ns Input signals are charged one time during 20	160		mA	
	I _{CC2NS}	CKE ≥ V _{IH(min)} , CK ≤ V _{IL(max)} , t _{CC} = ∞ Input signals are stable	80		mA	
Active standby current in power- down mode	I _{CC3P}	CKE ≥ V _{IL(max)} , t _{CC} = 10ns	40		mA	
	I _{CC3PS}	CKE & CK ≤ V _{IL(max)} , t _{CC} = ∞	40			
Active standby in current non power-down mode	I _{CC3N}	CKE ≥ V _{IH(min)} , CS ≥ V _{IH(min)} , t _{CC} = 10ns Input signals are charged one time during 20ns	240		mA	
	I _{CC3NS}	CKE ≥ V _{IH(min)} , CK ≤ V _{IL(max)} , t _{CC} = ∞ input signals are stable	200		mA	
Operating current (Burst mode)	I _{CC4}	I _O = mA Page burst 4 Banks activated t _{CCD} = 2CK	880	880	mA	1
Refresh current	I _{CC5}	t _{RC} ≥ t _{RC(min)}	1600	1600	mA	2
Self refresh current	I _{CC6}	CKE ≤ 0.2V	16		mA	

Notes:

1. Measured with outputs open.
2. Refresh period is 64ms.



ORDERING INFORMATION

Part Number	Clock Speed	CAS Latency	Height*
W3DG6418V10D2xx	100MHz	CL=2	30.48 (1.20")
W3DG6418V7D2xx	133MHz	CL=2	30.48 (1.20")
W3DG6418V75D2xx	133MHz	CL=3	30.48 (1.20")

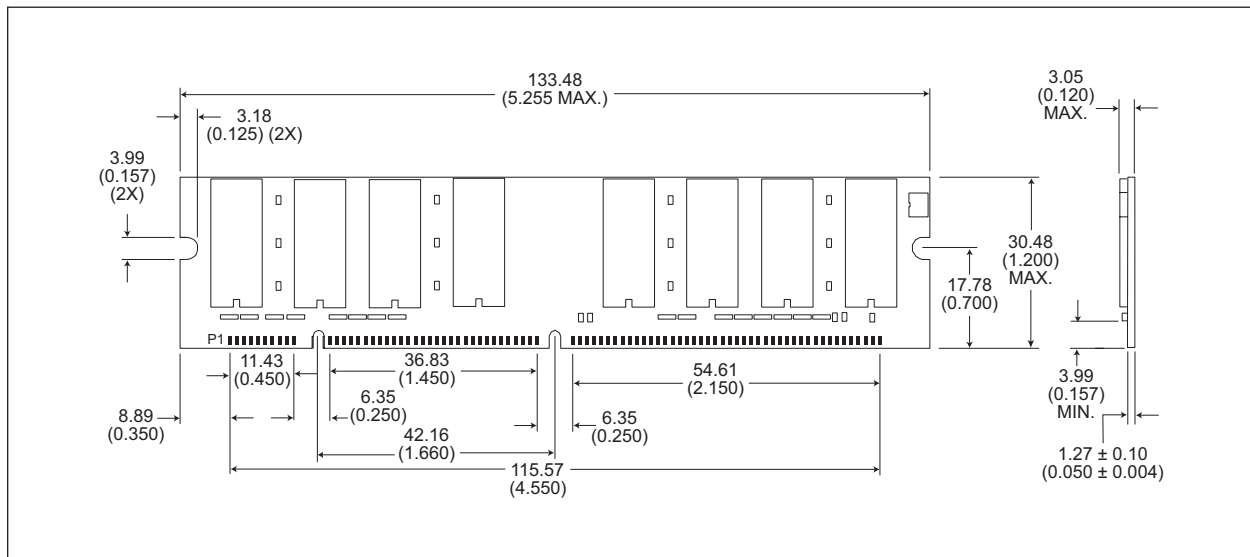
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W3DG6318V7D2xx	133MHz	CL=2	30.48 (1.20")
W3DG6318V75D2xx	133MHz	CL=3	30.48 (1.20")

Note: WP (write protect) is available on pin 81.

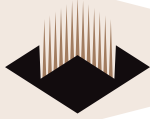
INDUSTRIAL TEMPERATURE

Ordering Information	Clock Speed	CAS Latency	Height*
W3DG6418V10D2I-xx	100MHz	CL=2	30.48 (1.20")
W3DG6418V7D2I-xx	133MHz	CL=2	30.48 (1.20")
W3DG6418V75D2I-xx	133MHz	CL=3	30.48 (1.20")

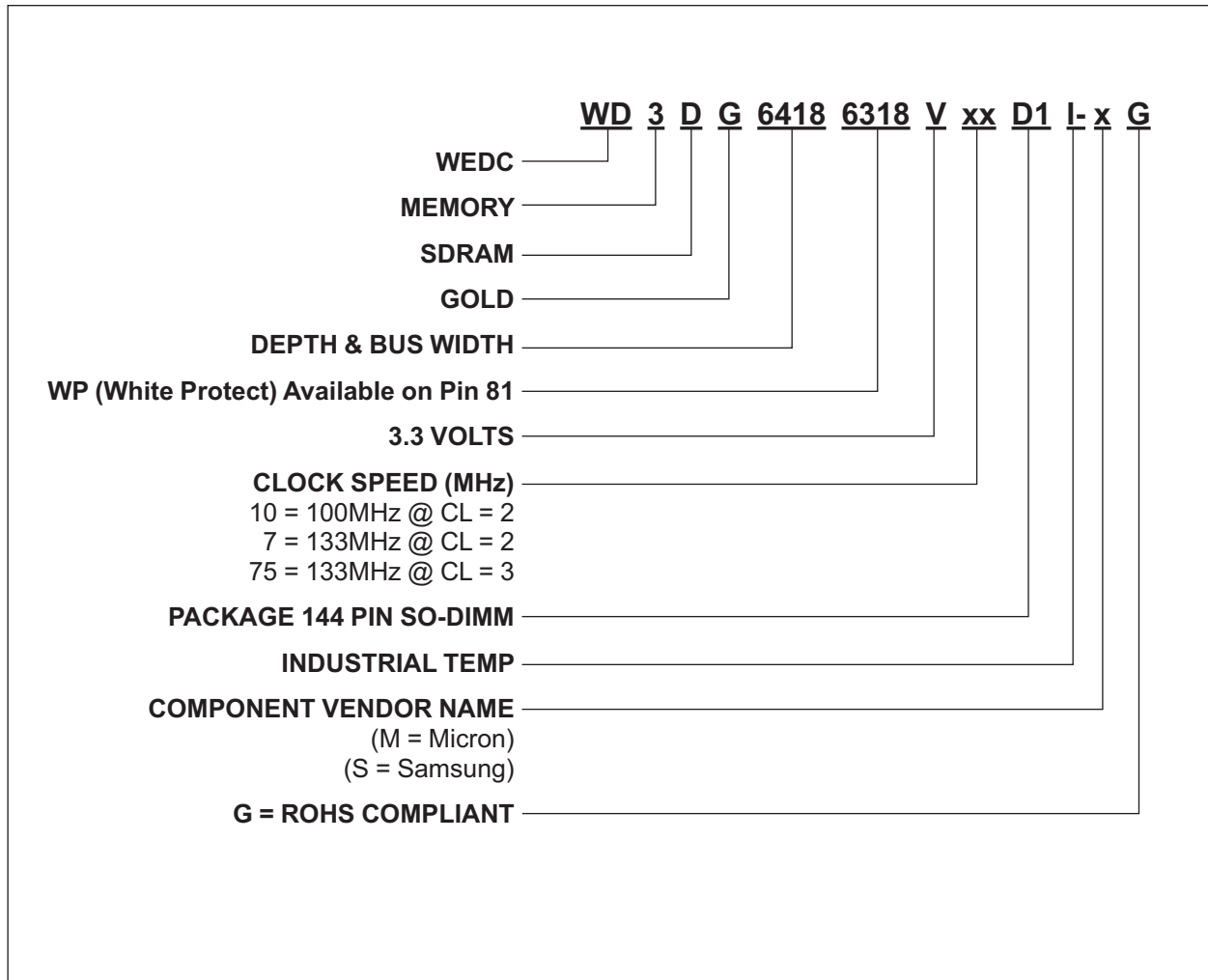
PACKAGE DIMENSIONS



* ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES).



PART NUMBERING GUIDE



**Document Title**

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Revision History

Rev #	History	Release Date	Status
Rev A	Created	12-6-01	Advanced
Rev B	Add "Part Number" to order info table on page 6	2-13-02	Advanced
Rev C	C.1 Added "WP" to pin 81 on pages 1, 3 & 6 C.2 Changed packate drawing on page 67	4-24-02	Advanced
Rev D	Corrected mechanical drawing	5-21-02	Advanced
Rev 0	0.1 Updated Cap & I _{DD} Specs 0.2 Removed "ED" from part number 0.3 Changed status from Advanced to Preliminary	6-04	Preliminary
Rev 1	1.0 Added new notes for <ul style="list-style-type: none">• RoHS compliant option• Vendor source control• Industrial temp option 1.1 Added new part number guide 1.2 Added industrial ordering info	3-06	Preliminary